

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_C = +25^\circ C$
80V	16m Ω @ $V_{GS} = 10V$	35A
	22m Ω @ $V_{GS} = 6V$	30A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

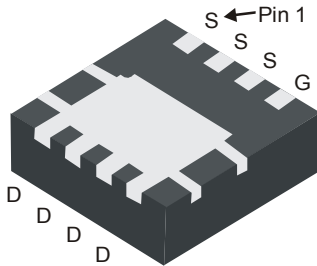
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

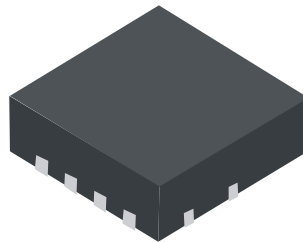
- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Excellent $Q_{gd} \times R_{DS(ON)}$ Product (FOM)
- Advanced Technology for DC/DC converts
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS (Avalanche) rated
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

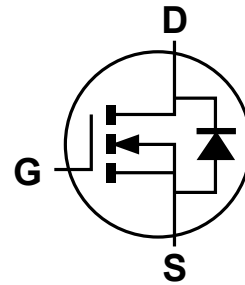
- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.008 grams (approximate)



Bottom View



Top View



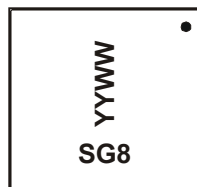
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT8012LFG-7	POWERDI3333-8	2,000/Tape & Reel
DMT8012LFG-13	POWERDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



SG8 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last digit of year (ex: 13 = 2013)
 WW = Week code (01 ~ 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	80	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	9.5 7.6	A
	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	35 28	A
Maximum Continuous Body Diode Forward Current (Note 5)	I_S	2	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)	I_{DM}	80	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	$T_A = +25^\circ\text{C}$	2.2
		$T_C = +25^\circ\text{C}$	30
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	Steady State	57
		$t < 10\text{s}$	35
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	4.2	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	80	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 64\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	1	1.5	3	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	13	16	m Ω	$V_{GS} = 10\text{V}, I_D = 12\text{A}$
		—	14	22		$V_{GS} = 6\text{V}, I_D = 6\text{A}$
Diode Forward Voltage	V_{SD}	—	0.9	1.2	V	$V_{GS} = 0\text{V}, I_S = 12\text{A}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	1949	—	pF	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	177	—		
Reverse Transfer Capacitance	C_{rss}	—	10	—		
Gate resistance	R_g	—	0.7	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	15	—	nC	$V_{DS} = 40\text{V}, I_D = 12\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	34	—		
Gate-Source Charge	Q_{gs}	—	6	—		
Gate-Drain Charge	Q_{gd}	—	4.5	—		
Turn-On Delay Time	$t_{D(on)}$	—	4.9	—	nS	$V_{DD} = 40\text{V}, V_{GS} = 10\text{V}, I_D = 12\text{A}, R_G = 1.6\Omega,$
Turn-On Rise Time	t_r	—	3.8	—		
Turn-Off Delay Time	$t_{D(off)}$	—	16.5	—		
Turn-Off Fall Time	t_f	—	3.5	—		
Body Diode Reverse Recovery Time	t_{rr}	—	30.2	—	nS	$I_F = 12\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{rr}	—	34.6	—	nC	

- Notes:
- $R_{\theta JA}$ is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

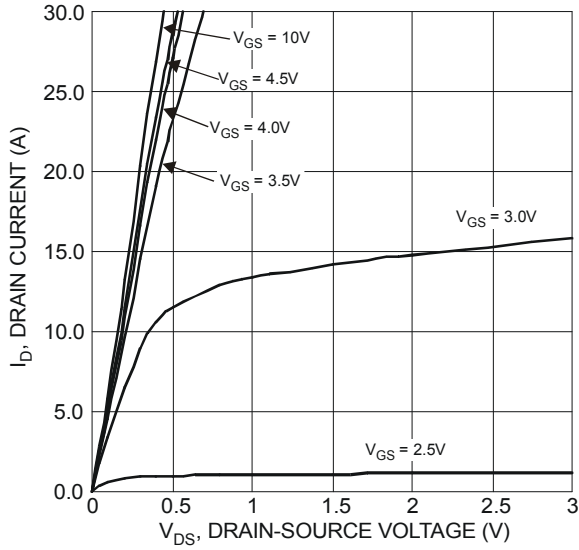


Figure 1 Typical Output Characteristics

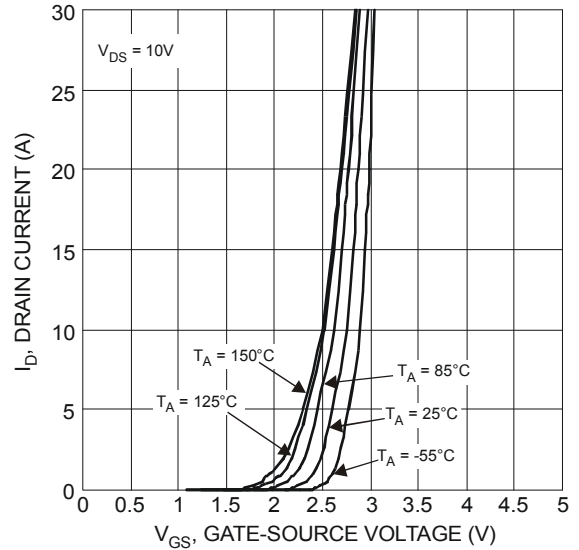


Figure 2 Typical Transfer Characteristics

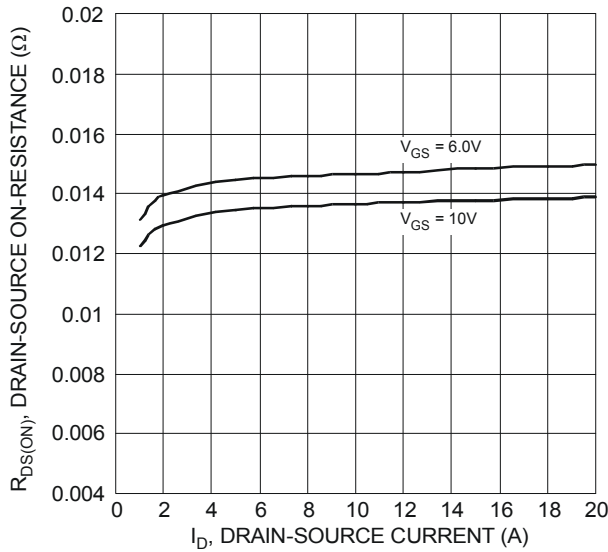


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

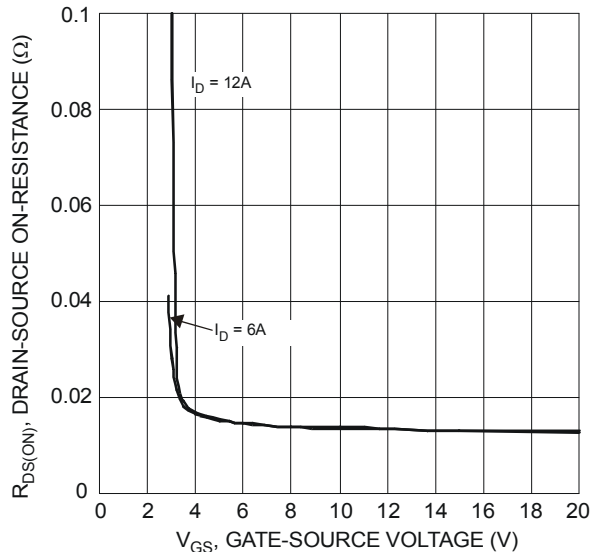


Figure 4 Typical Transfer Characteristics

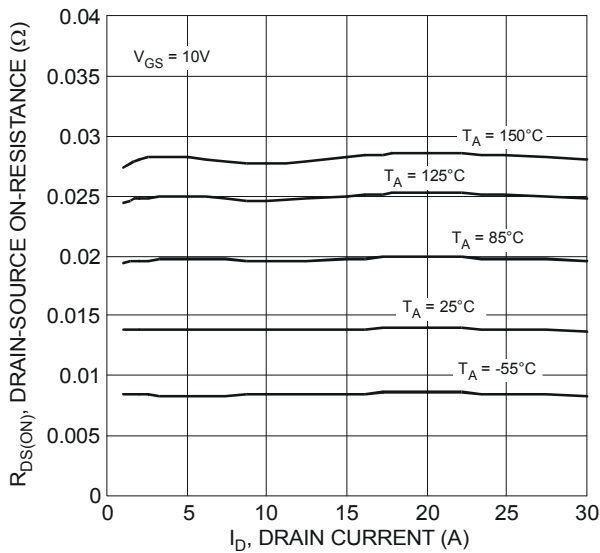


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

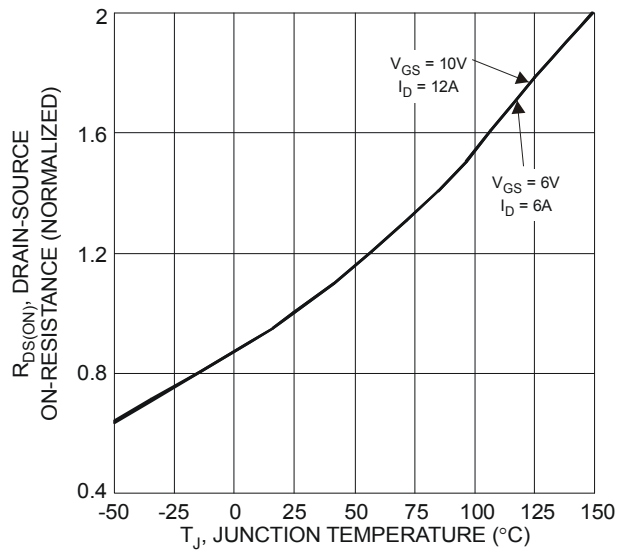


Figure 6 On-Resistance Variation with Temperature

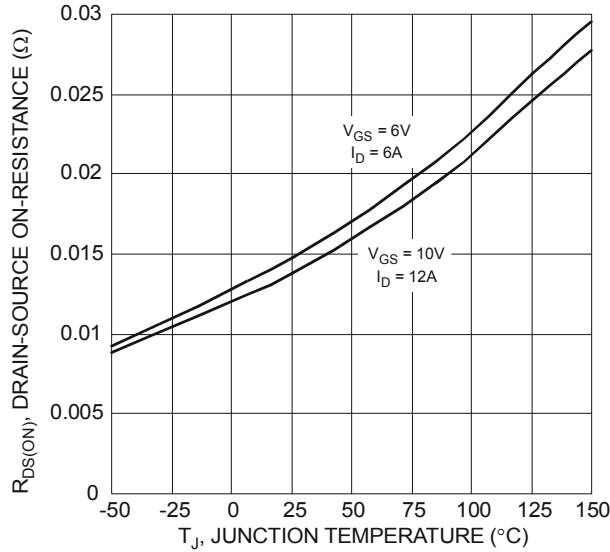


Figure 7 On-Resistance Variation with Temperature

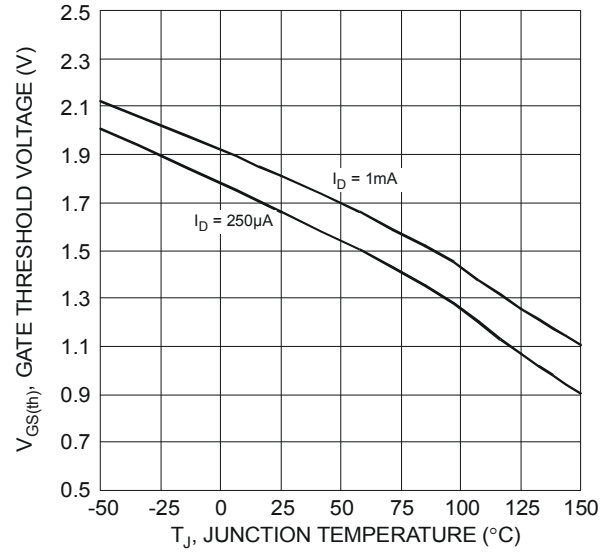


Figure 8 Gate Threshold Variation vs. Ambient Temperature

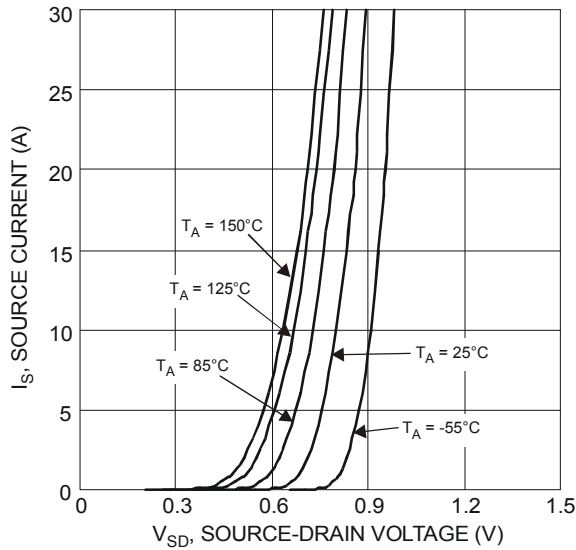


Figure 9 Diode Forward Voltage vs. Current

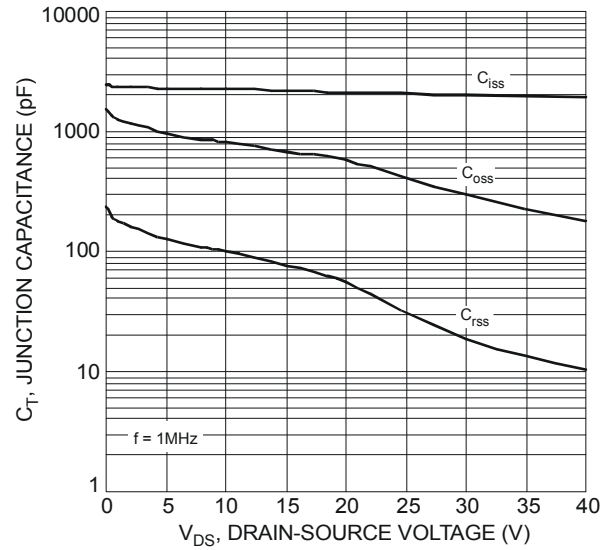


Figure 10 Typical Junction Capacitance

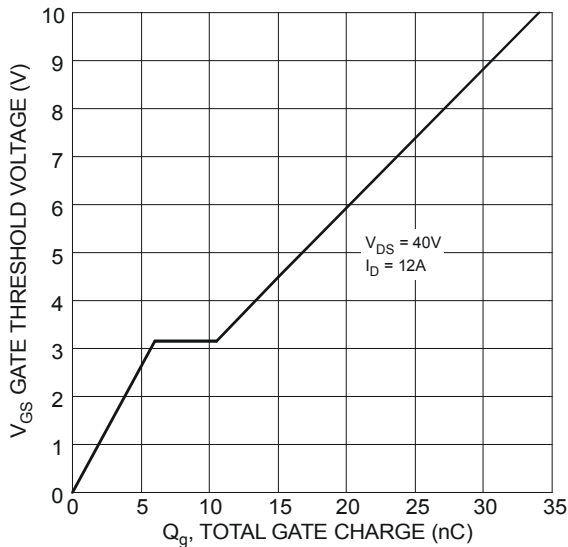


Figure 11 Gate Charge

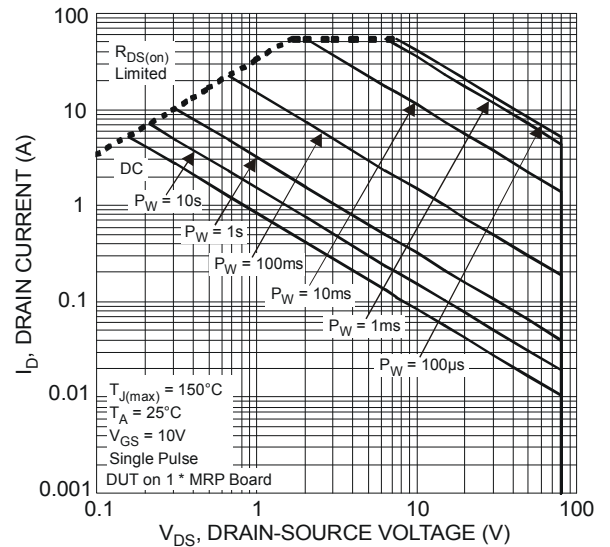


Figure 12 SOA, Safe Operation Area

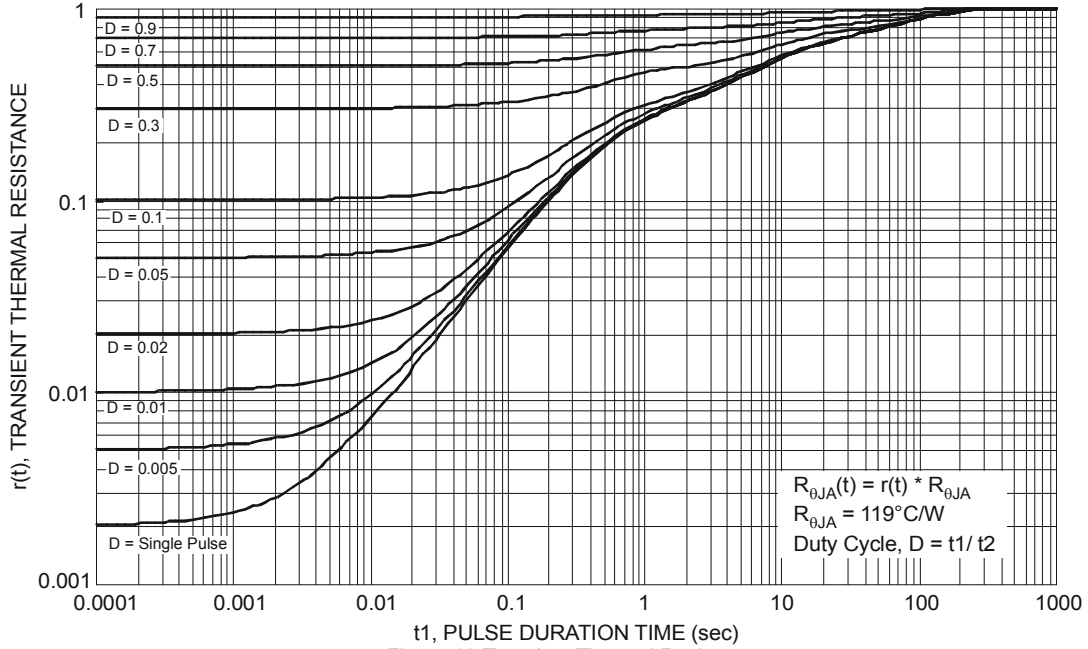
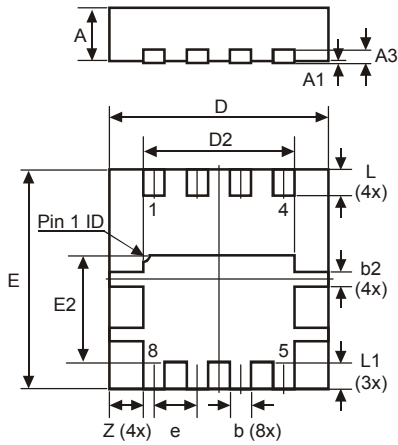


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

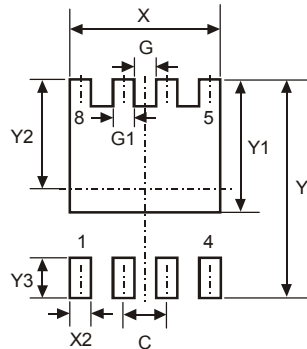
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



POWERDI [®] 3333-8			
Dim	Min	Max	Typ
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
L	0.35	0.45	0.40
L1	-	-	0.39
e	-	-	0.65
Z	-	-	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for latest version.



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420

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- Подбор аналогов;
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- Техническая поддержка проекта;
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